

# **Power Transistors**

# NPN Silicon DPAK For Surface Mount Applications

# **NJD2873**

Designed for high-gain audio amplifier applications.

### **Features**

- High DC Current Gain
- Low Collector-Emitter Saturation Voltage
- High Current-Gain Bandwidth Product
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### **MAXIMUM RATINGS**

Symbol	Rating	Value	Unit
V <sub>CB</sub>	Collector-Base Voltage	50	Vdc
V <sub>CEO</sub>	Collector-Emitter Voltage	50	Vdc
V <sub>EB</sub>	Emitter-Base Voltage	5	Vdc
I <sub>C</sub>	Collector Current – Continuous	2	Adc
I <sub>CM</sub>	Collector Current - Peak	3	Adc
Ι <sub>Β</sub>	Base Current	0.4	Adc
P <sub>D</sub>	Total Device Dissipation @ T <sub>C</sub> = 25 °C Derate above 25 °C	15 0.1	W W/°C
P <sub>D</sub>	Total Device Dissipation @ T <sub>A</sub> = 25 °C* Derate above 25 °C	1.68 0.011	W W/°C
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-65 to +175	°C
НВМ	ESD - Human Body Model	3B	V
MM	ESD - Machine Model	С	V

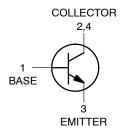
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1

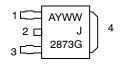
# SILICON POWER TRANSISTORS 2 AMPERES 50 VOLTS 15 WATTS



DPAK CASE 369C STYLE 1



### MARKING DIAGRAM



A = Assembly Location

Y = Year WW = Work Week G = Pb-Free Device

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NJD2873T4G	DPAK (Pb-Free)	2,500 Units / Reel
NJVNJD2873T4G	DPAK (Pb-Free)	2,500 Units / Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# THERMAL CHARACTERISTICS

Sy	ymbol	Characteristic	Max	Unit
	R <sub>θJC</sub> R <sub>θJA</sub>	Thermal Resistance Junction-to-Case Junction-to-Ambient (Note 1)	10 89.3	°C/W

<sup>1.</sup> These ratings are applicable when surface mounted on the minimum pad sizes recommended.

# **ELECTRICAL CHARACTERISTICS** ( $T_C = 25$ °C unless otherwise noted)

Symbol	Characteristic	Min	Max	Unit
OFF CHARACTERISTICS				
V <sub>CEO(sus)</sub>	Collector-Emitter Sustaining Voltage (Note 2) $(I_C = 10 \text{ mAdc}, I_B = 0)$	50	-	Vdc
I <sub>CBO</sub>	Collector Cutoff Current (V <sub>CB</sub> = 50 Vdc, I <sub>E</sub> = 0)	-	100	nAdc
I <sub>EBO</sub>	Emitter Cutoff Current (V <sub>BE</sub> = 5 Vdc, I <sub>C</sub> = 0)	-	100	nAdc
ON CHARACT	TERISTICS			
h <sub>FE</sub>	DC Current Gain (Note 2) $ \begin{array}{l} (I_C=0.5 \text{ A, V}_{CE}=2 \text{ V}) \\ (I_C=2 \text{ Adc, V}_{CE}=2 \text{ Vdc}) \\ (I_C=0.75 \text{ Adc, V}_{CE}=1.6 \text{ Vdc, } -40 \text{ °C} \leq T_J \leq 150 \text{ °C}) \end{array} $	120 40 80	360 - 360	-
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage (Note 2) (I <sub>C</sub> = 1 A, I <sub>B</sub> = 0.05 A)	-	0.3	Vdc
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage (Note 2) (I <sub>C</sub> = 1 A, I <sub>B</sub> = 0.05 Adc)	-	1.2	Vdc
V <sub>BE(on)</sub>	Base-Emitter On Voltage (Note 2) $ (I_C = 1 \text{ Adc, } V_{CE} = 2 \text{ Vdc}) \\ (I_C = 0.75 \text{ Adc, } V_{CE} = 1.6 \text{ Vdc, } -40 \text{ °C} \leq T_J \leq 150 \text{ °C}) $	-	1.2 0.95	Vdc
DYNAMIC CHARACTERISTICS				
f <sub>T</sub>	Current-Gain – Bandwidth Product (Note 3) (I <sub>C</sub> = 100 mAdc, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 10 MHz)	65	-	MHz
C <sub>ob</sub>	Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 0.1 MHz)	-	80	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300  $\mu$ s, Duty Cycle  $\approx$  2%.

3.  $f_T = |h_{fe}| \cdot f_{test}$ .

# **TYPICAL CHARACTERISTICS**

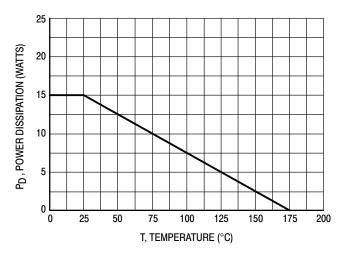


Figure 1. Power Derating

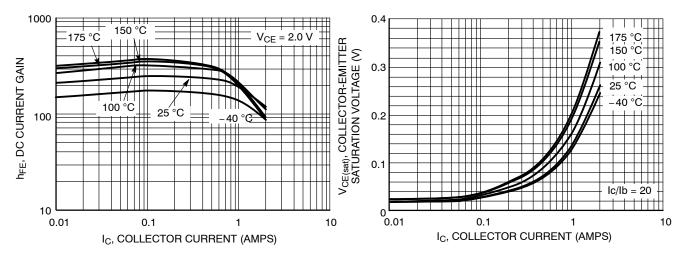


Figure 2. DC Current Gain

Figure 3. Collector-Emitter Saturation Voltage

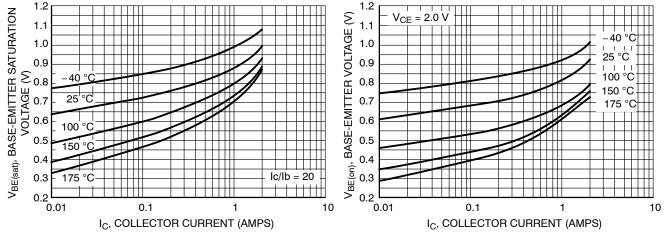


Figure 4. Base-Emitter Saturation Voltage

Figure 5. Base-Emitter Voltage

# TYPICAL CHARACTERISTICS (continued)

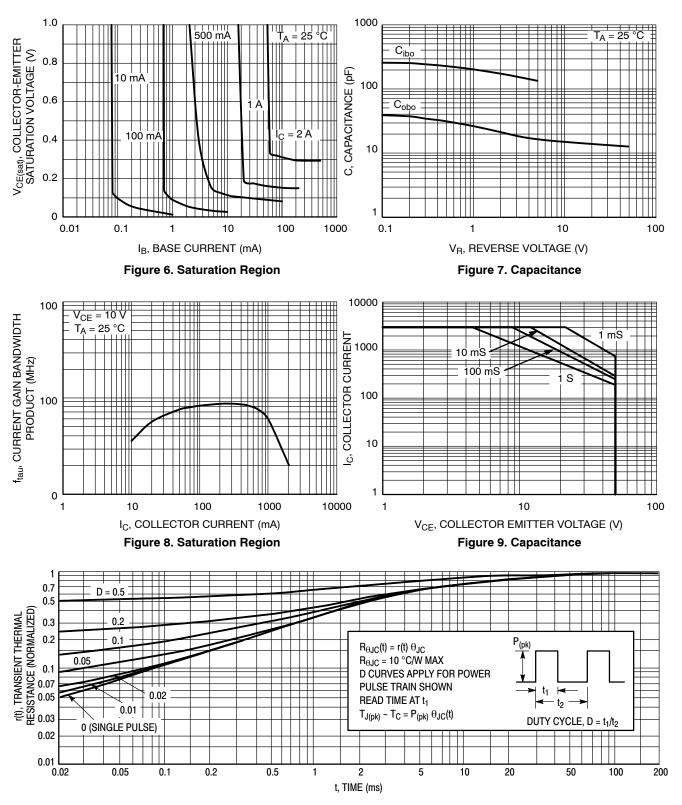


Figure 10. Thermal Response

# **REVISION HISTORY**

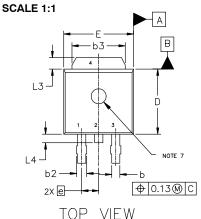
Revision	n Description of Changes	
19	Rebranded the Data Sheet to <b>onsemi</b> format.	6/26/2025

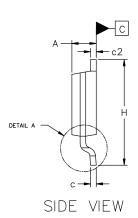




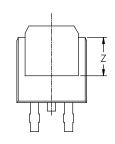
### DPAK3 6.10x6.54x2.28, 2.29P CASE 369C **ISSUE J**

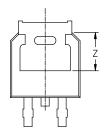
**DATE 12 AUG 2025** 

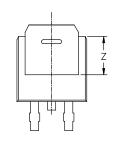


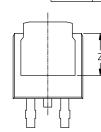


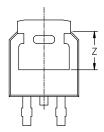
	MILLIMETERS				
DIM	MIN	NOM	MAX		
А	2.18	2.28	2.38		
A1	0.00		0.13		
b	0.63	0.76	0.89		
b2	0.72	0.93	1.14		
b3	4.57	5.02	5.46		
С	0.46	0.54	0.61		
c2	0.46	0.54	0.61		
D	5.97	6.10	6.22		
E	6.35	6.54	6.73		
е	:	2.29 BSC			
Н	9.40	9.91	10.41		
L	1.40	1.59	1.78		
L1	2.90 REF				
L2	0.51 BSC				
L3	0.89		1.27		
L4			1.01		
Z	3.93				











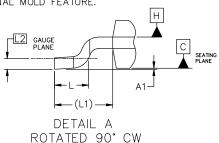
BOTTOM VIEW

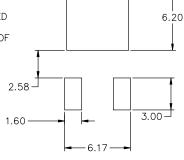
ALTERNATE CONSTRUCTIONS

### NOTES:

- DIMENSIONING AND TOLERANCING ASME Y14.5M, 2018.

- CONTROLLING DIMENSION: MILLIMETERS.
  THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR
  BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15mm PER SIDE.
- DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- DATUMS A AND B ARE DETERMINED AT DATUM PLANE H. OPTIONAL MOLD FEATURE.





-5.80

RECOMMENDED MOUNTING FOOTPRINT\*

\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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DESCRIPTION:	DPAK3 6.10x6.54x2.28, 2.2	9P	PAGE 1 OF 2

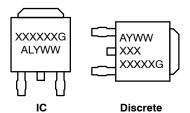
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# DPAK3 6.10x6.54x2.28, 2.29P

CASE 369C ISSUE J

**DATE 12 AUG 2025** 

# GENERIC MARKING DIAGRAM\*



XXXXXX = Device Code

A = Assembly Location

L = Wafer Lot

Y = Year

WW = Work Week

G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. GATE		PIN 1. CATHODE	PIN 1. GATE
2. COLLECTOR	2. DRAIN		2. ANODE	2. ANODE
3. EMITTER	3. SOURCE		3. GATE	3. CATHODE
4. COLLECTOR	4. DRAIN		4. ANODE	4. ANODE

STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:
PIN 1. MT1	PIN 1. GATE	PIN 1. N/C	PIN 1. ANODE	PIN 1. CATHODE
2. MT2	<ol><li>COLLECTOR</li></ol>	<ol><li>CATHODE</li></ol>	2. CATHODE	2. ANODE
<ol><li>GATE</li></ol>	<ol><li>EMITTER</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>RESISTOR ADJUST</li></ol>	<ol><li>CATHODE</li></ol>
4. MT2	<ol><li>COLLECTOR</li></ol>	<ol><li>CATHODE</li></ol>	4. CATHODE	<ol><li>ANODE</li></ol>

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